

# **Final Product Change Notification**

Issue Date: 17-Mar-2017 Effective Date: 30-Jun-2017

Here's your personalized quality information concerning products Digi-Key purchased from Nexperia.

For detailed information we invite you to view this

notification online



# **Change Category**

[] Wafer Fab Process [] Assembly[] Product Marking [X] Test [] Design

Process Location
[] Wafer Fab Materials [] Assembly[] Mechanical []Test [] Errata

Materials Specification Process

[] Wafer Fab Location [X] [] Test [] Electrical Assembly Packing/Shipping/Labeling Equipment spec./Test Location coverage

Release Nexperia
Assembly and Test
Malaysia Facility as 2nd
Source for PowerMOS

# **Details of this Change**

Multi Site Assembly and Test of LFPAK56 (SOT669) will be supported by Nexperia Assembly and Test in Malaysia (ATSN) in addition to Nexperia Assembly and Test in the Philippines (ATCB).

# Why do we Implement this Change

To meet Customer requirements for second sourcing of production as a business contingency. From implementation date Nexperia will have increased capacity provided by two manufacturing locations for our LFPAK56 outline, ATCB Philippines and ATSN Malaysia.

### **Identification of Affected Products**

Top side marking

Four Marking codes will exist following this introduction identifying the four sources of DMAN/VIS wafers and ATCB/ATSN Assembly and Test (Prt, PEt, Prm and PEm).

### **Product Availability**

Sample Information

Samples are available upon request

Production

Planned first shipment 30-Jun-2017

# **Impact**

no impact to the product's functionality anticipated.

None. No impact on form, fit or function. Same process flow, materials and final test.

#### **Data Sheet Revision**

No impact to existing datasheet

#### **Disposition of Old Products**

N/A

### **Related Notifications**

Notification Issue Date Effective Date Title

201702001F01U01 01-Mar-2017 14-Jun-2017 Release of 2nd source assembly for BUK9Y12-40E

#### **Timing and Logistics**

Your acknowledgement of this change, conform JEDEC J-STD-046, is expected till 16-Apr-2017.

#### Remarks

The qualification of Power MOS devices in ATSN has been successfully carried out using PH6030DLV as the Structural Group Leader. This type has been in production since Q1 2016. However, the varying devices utilise different top clips, Nexperia plan to perform further qualifications to expand reliability knowledge and parametric performance data. (As attached Qual Plan).

# **Contact and Support**

For all inquiries regarding the ePCN tool application or access issues, please contact Nexperia "Global Quality Support Team".

For all Quality Notification content inquiries, please contact your local Nexperia Sales Support team.

For specific questions on this notice or the products affected please contact our specialist directly:

e-mail address powermos.pcn@nexperia.com

At Nexperia B.V we are constantly striving to improve our product and processes to ensure they reach the highest possible Quality Standards.

Nexperia Quality Management Team.

**Manchester:** powermos.pcn@nexperia.com **Nijmegen:** logic.helpdesk@Nexperia.com

Hamburg: DiscrQA.Helpdesk.GA-Products@nexperia.com

# **About Nexperia B.V**

We at Nexperia are the efficiency semiconductor company. We deliver over 70 billion products a year and as such service thousands of global customers, both directly and through our extensive network of channel partners. We are at the heart of billions of electronic devices in the Automotive, Mobile, Industrial, Consumer, Computing, and Communication Infrastructure segments.

You have received this email because you are a designated contact or subscribed to Nexperia Quality Notifications. Nexperia shall not be held liable if this Notification is not correctly distributed within your organization.

This message has been automatically distributed. Please do not reply.

Nexperia B.V.
Jonkerbosplein 52 6534 AB Nijmegen, The Netherlands
© 2017 Nexperia. All rights reserved.

Changed Orderable Part#	Changed Part 12NC	Changed Part Number	Changed Part Description	Package Outline	Package Name	Status	Product Line
PSMN045-80YS,115	934064149115	PSMN045-80YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN039-100YS,115	934064535115	PSMN039-100YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN020-100YS,115	934064431115	PSMN020-100YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN2R2-25YLC,115	934065199115	PSMN2R2-25YLC	9657 Trench 7	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN2R4-30YLDX	934067965115	PSMN2R4-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN4R0-40YS,115	934063937115	PSMN4R0-40YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN025-80YLX	934069902115	PSMN025-80YL	Trench 6 (SOT669)	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN6R0-30YL,115	934063076115	PSMN6R0-30YL	<=30V N CH TRENCHFET	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN026-80YS,115	934063933115	PSMN026-80YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN014-40YS,115	934064146115	PSMN014-40YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN069-100YS,115	934064536115	PSMN069-100YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN1R2-25YLC,115	934065197115	PSMN1R2-25YLC	9657 Trench 7	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN6R1-30YLDX	934067798115	PSMN6R1-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN3R0-30YLDX	934067966115	PSMN3R0-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN8R3-40YS,115	934063936115	PSMN8R3-40YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN017-60YS,115	934064399115	PSMN017-60YS	9656 TRENCH 6	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN2R2-30YLC,115	934065191115	PSMN2R2-30YLC	9657 Trench 7	SOT669	LFPAK	RFS	<b>BL MOS Discretes</b>
PSMN041-80YLX	934067516115	PSMN041-80YL	9656R5	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN7R5-30YLDX	934067967115	PSMN7R5-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN5R6-60YLX	934069895115	PSMN5R6-60YL	Trench 6 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN2R0-25YLDX	934069912115	PSMN2R0-25YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN2R6-30YLC,115	934065192115	PSMN2R6-30YLC	9657 Trench 7	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN2R0-30YLDX	934067964115	PSMN2R0-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN1R4-30YLDX	934068236115	PSMN1R4-30YLD	Trench 9 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN7R5-60YLX	934069896115	PSMN7R5-60YL	Trench 6 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN021-100YLX	934069906115	PSMN021-100YL	Trench 6 (SOT669)	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN7R0-30YL,115	934063077115	PSMN7R0-30YL	<=30V N CH TRENCHFET	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN8R5-60YS,115	934064402115	PSMN8R5-60YS	9656 TRENCH 6	SOT669	LFPAK	RFS	BL MOS Discretes
PSMN030-60YS,115	934064398115	PSMN030-60YS	9656 TRENCH 6	SOT669	LFPAK	RFS	BL MOS Discretes